**Product data sheet** 

# 1. General description

PNP low V<sub>CEsat</sub> transistor in a SOT89 plastic package.

NPN complement: PBSS4350X

## 2. Features and benefits

- SOT89 (SC-62) package
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability: I<sub>C</sub> and I<sub>CM</sub>
- · Higher efficiency leading to less heat generation
- Reduced printed-circuit board requirements
- AEC-Q101 qualified

# 3. Applications

- Power management
  - · DC/DC converters
  - Supply line switching
  - Battery charger
  - LCD backlighting
- Peripheral drivers
  - Driver in low supply voltage applications (e.g. lamps and LEDs)
  - Inductive load driver (e.g. relays, buzzers and motors)

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-50	V
I <sub>C</sub>	collector current		-	-	-3	Α
I <sub>CM</sub>	peak collector current	limited by T <sub>j(max)</sub>	-	-	-5	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -2 A; $I_B$ = -200 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	90	135	mΩ



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# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		С
2	С	collector		
3	В	base	3 2 1	B—[
			SOT89	sym132

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
PBSS5350X	SOT89	plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89		

# 7. Marking

### Table 4. Marking codes

Type number	Marking code
PBSS5350X	S46

# 8. Limiting values

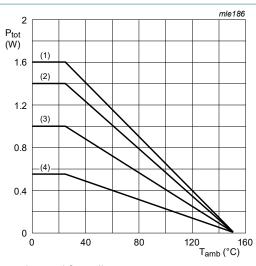
### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-50	V
$V_{CEO}$	collector-emitter voltage	open base		-	-50	V
$V_{EBO}$	emitter-base voltage	open collector		-	-5	V
I <sub>C</sub>	collector current			-	-3	А
I <sub>CM</sub>	peak collector current	limited by T <sub>j(max)</sub>		-	-5	Α
I <sub>B</sub>	base current			-	-0.5	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	550	mW
			[2]	-	1	W
			[3]	-	1.4	W
			[4]	-	1.6	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>. Device mounted on a ceramic printed-circuit board 7 cm<sup>2</sup>, single-sided copper, tin-plated.

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- (1) Ceramic PCB; 7 cm<sup>2</sup> mounting pad for collector (2) FR4 PCB; 6 cm<sup>2</sup> copper mounting pad for collector (3) FR4 PCB; 1 cm<sup>2</sup> copper mounting pad for collector

- (4) Standard footprint

**Power derating curves** Fig. 1.

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient	thermal resistance from	in free air	[1]	-	-	225	K/W
	junction to ambient	[2]	-	-	125	K/W	
		[3]	[3]	-	-	90	K/W
		[	[4]	-	-	80	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	16	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>. [3]
- Device mounted on a ceramic printed-circuit board 7 cm<sup>2</sup>, single-sided copper, tin-plated.

#### 50 V, 3 A PNP low VCEsat transistor

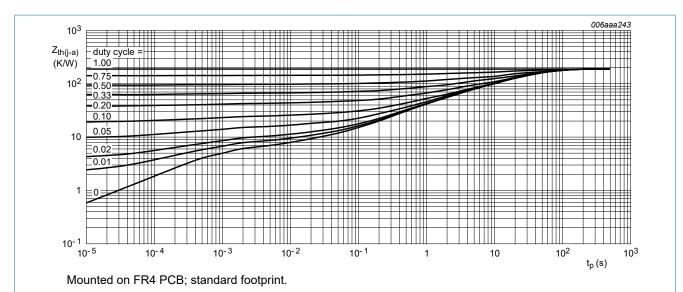
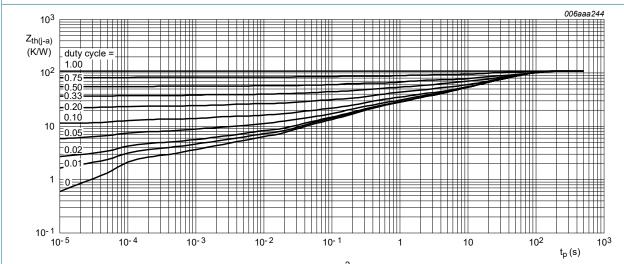


Fig. 2. Transient thermal impedance as a function of pulse duration; typical values



Mounted on FR4 PCB; mounting pad for collector 1 cm<sup>2</sup>

Fig. 3. Transient thermal impedance as a function of pulse duration; typical values

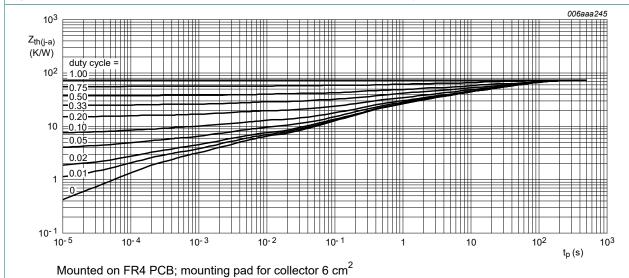


Fig. 4. Transient thermal impedance as a function of pulse duration; typical values

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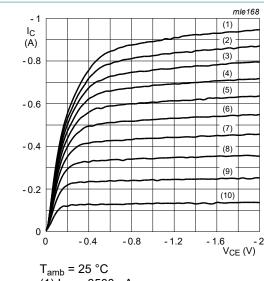
50 V, 3 A PNP low VCEsat transistor

# 10. Characteristics

## **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	$I_C = -100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	-50	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	$I_C = -10 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-50	-	-	V
V <sub>(BR)EBO</sub>	emitter-base breakdown voltage (collector open)	$I_E = -100 \ \mu A; I_C = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	-5	-	-	V
СВО	collector-base cut-off	V <sub>CB</sub> = -50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -50 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = -50 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
ЕВО	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; $I_{C}$ = 0.1 A; single pulse; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	200	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -0.5 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	200	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -1 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	200	-	450	
		$V_{CE}$ = -2 V; $I_{C}$ = -2 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	130	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -3 A; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	80	-	-	
V <sub>CEsat</sub>	collector-emitter	I <sub>C</sub> = -0.5 A; I <sub>B</sub> = -50 mA; T <sub>amb</sub> = 25 °C	-	-	-90	mV
	saturation voltage	I <sub>C</sub> = -1 A; I <sub>B</sub> = -50 mA; T <sub>amb</sub> = 25 °C	-	-	-180	mV
		I <sub>C</sub> = -2 A; I <sub>B</sub> = -100 mA; T <sub>amb</sub> = 25 °C	-	-	-320	mV
		$I_C$ = -2 A; $I_B$ = -200 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-270	mV
		$I_C$ = -3 A; $I_B$ = -300 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-390	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -2 A; $I_B$ = -200 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	90	135	mΩ
V <sub>BEsat</sub>	base-emitter saturation	$I_C = -2 \text{ A}; I_B = -100 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	-1.1	V
	voltage	$I_C$ = -3 A; $I_B$ = -300 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-1.2	V
V <sub>BEon</sub>	base-emitter turn-on voltage	V <sub>CE</sub> = -2 V; I <sub>C</sub> = -1 A; T <sub>amb</sub> = 25 °C	-	-	-1.1	V
<sup>E</sup> T	transition frequency	$V_{CE}$ = -5 V; $I_{C}$ = -100 mA; f = 100 MHz; $T_{amb}$ = 25 °C	100	-	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$	-	-	35	pF

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(1)  $I_B = -3500 \mu A$ 

(2)  $I_B = -3150 \mu A$ 

 $(3) I_B = -2800 \mu A$ 

 $(4) I_B = -2450 \mu A$ 

(5)  $I_B = -2100 \,\mu A$ 

(6)  $I_B = -1750 \,\mu A$ 

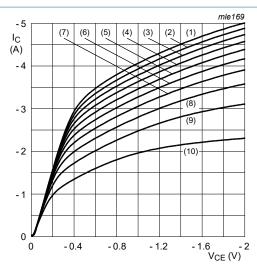
 $(7) I_B = -1400 \mu A$ 

(8)  $I_B = -1050 \mu A$ 

(9)  $I_B = -700 \mu A$ 

(10)  $I_B = -350 \mu A$ 

Fig. 5. Collector current as a function of collectoremitter voltage; typical values



 $T_{amb}$  = 25 °C

(1)  $I_B = -140 \text{ mA}$ 

(2)  $I_B = -126 \text{ mA}$ 

(3)  $I_B = -112 \text{ mA}$ (4)  $I_B = -98 \text{ mA}$ 

 $(5) I_{B}^{-} = -84 \text{ mA}$ 

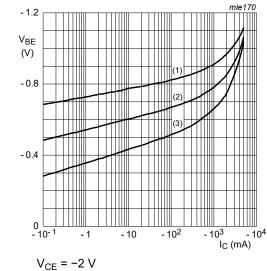
(6)  $I_B = -70 \text{ mA}$  $(7) I_B = -56 \text{ mA}$ 

(8)  $I_B = -42 \text{ mA}$ 

(9)  $I_B = -28 \text{ mA}$ 

 $(10) I_B = -14 mA$ 

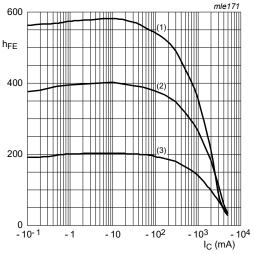
Fig. 6. Collector current as a function of collectoremitter voltage; typical values



(1)  $T_{amb} = -55 \, ^{\circ}C$ 

(2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = 100 °C

Fig. 7. Base-emitter voltage as a function of collector current; typical values



 $V_{CE} = -2 V$ (1)  $T_{amb} = 100 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig. 8. DC current gain as a function of collector current; typical values

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## 50 V, 3 A PNP low VCEsat transistor

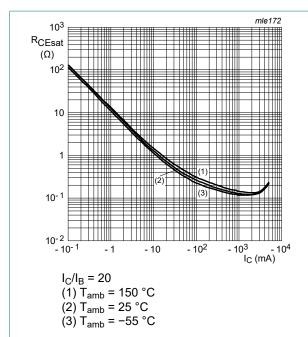


Fig. 9. Equivalent on-resistance as a function of collector current; typical values

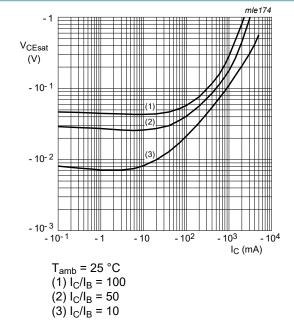


Fig. 11. Collector-emitter saturation voltage as a function of collector current; typical values

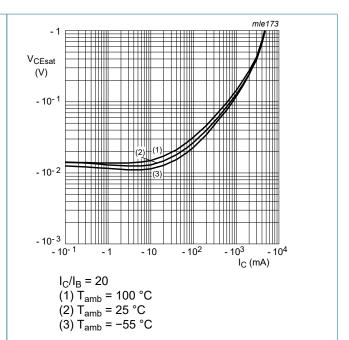


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

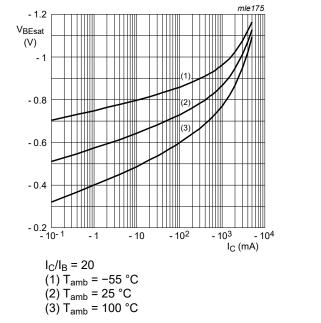


Fig. 12. Base-emitter saturation voltage as a function of collector current; typical values

## 11. Test information

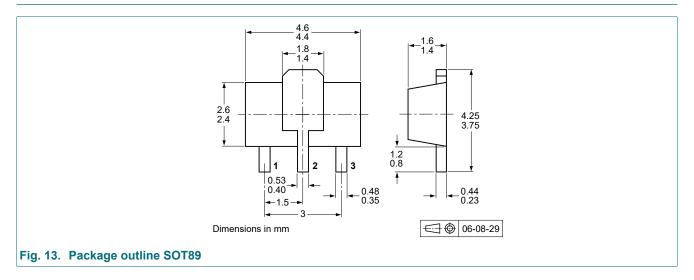
#### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

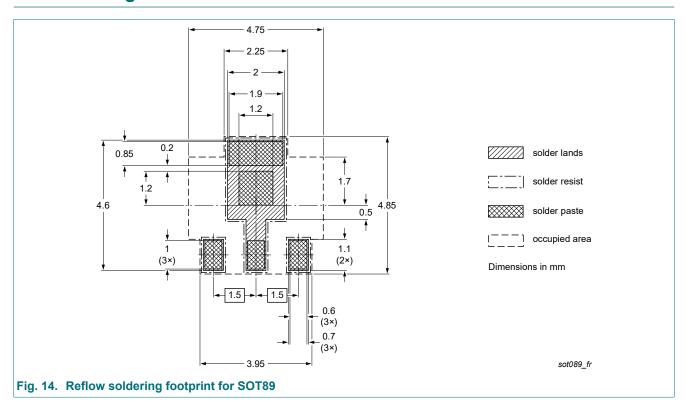
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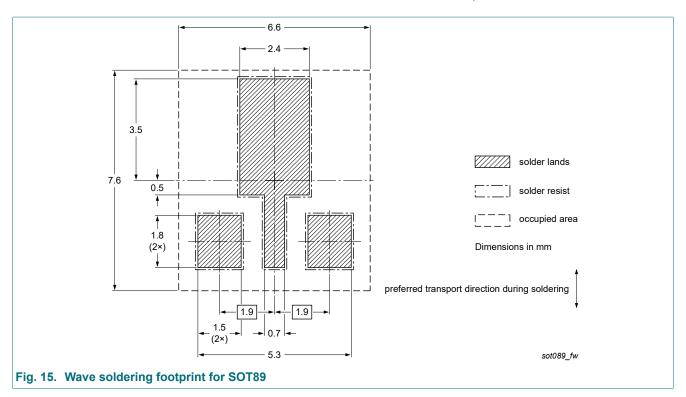
# 12. Package outline



# 13. Soldering



## 50 V, 3 A PNP low VCEsat transistor



## 50 V, 3 A PNP low VCEsat transistor

# 14. Revision history

#### **Table 8. Revision history**

Table of Revision metery								
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PBSS5350X v.3	20220516	Product data sheet	-	PBSS5350X v.2				
Modifications:	Nexperia.	The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia.  Legal texts have been adapted to the new company name where appropriate.						
PBSS5350X v.2	20041104	Product data sheet	-	PBSS5350X v.1				
PBSS5350X v.1	20031121	Product data sheet	-	-				

#### 50 V, 3 A PNP low VCEsat transistor

## 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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PBSS5350X

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## 50 V, 3 A PNP low VCEsat transistor

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